

Silicon PNP Power Transistors

2N5611A

DESCRIPTION

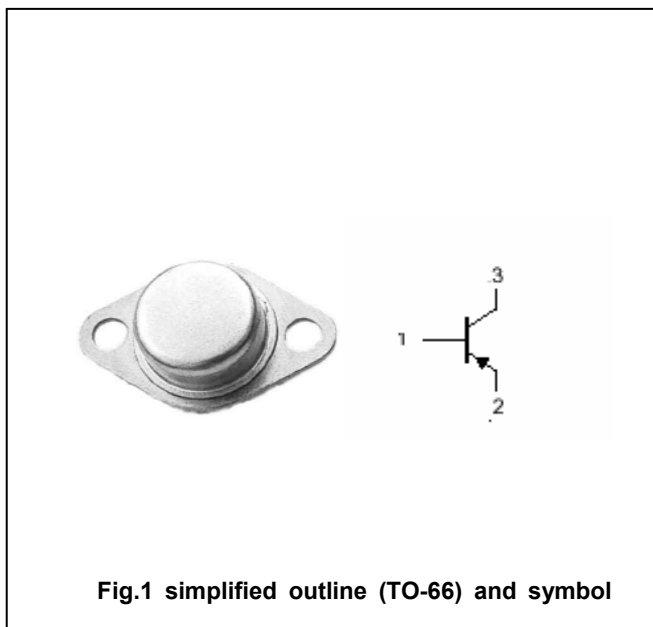
- With TO-66 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For general-purpose amplifier ;
and switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-120	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-5	A
P _D	Total power dissipation	T _C =25□	25	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~150	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	4.37	□/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-50mA ; I _B =0	-100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A; I _B =-0.1A			-0.5	V
V _{BE}	Base-emitter on voltage	I _C =-2.5A ; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =Rated V _{CBO} ; I _E =0			-0.1	mA
I _{CEO}	Collector cut-off current	V _{CE} = Rated V _{CEO} , I _B =0			-1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-2.5A ; V _{CE} =-5V	30		150	
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-10V	60			MHz

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PACKAGE OUTLINE



Fig.2 outline dimensions